

Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 5.3~5.9GHz
- Typical Pout : 57.5dBm
- Typical Gain: 11.5dB
- Typical PAE: 52%
- Bias: 50V@18A
- Package: Metal Ceramic

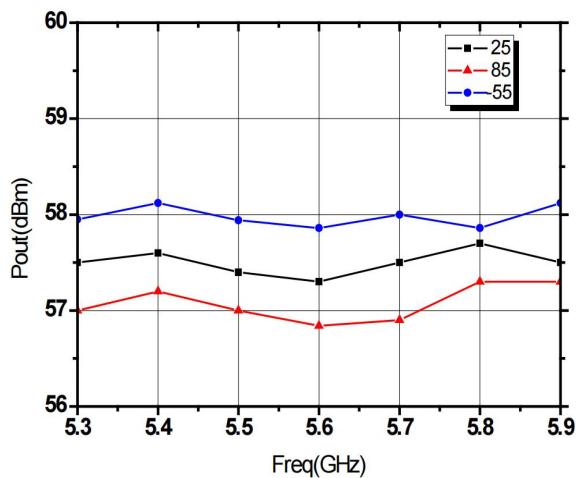


Electrical Specifications (TA=25°C, Vd=50V, Vg= -3V~-2V, F: 5.3~5.9GHz, PL=100us, D.C=10%)

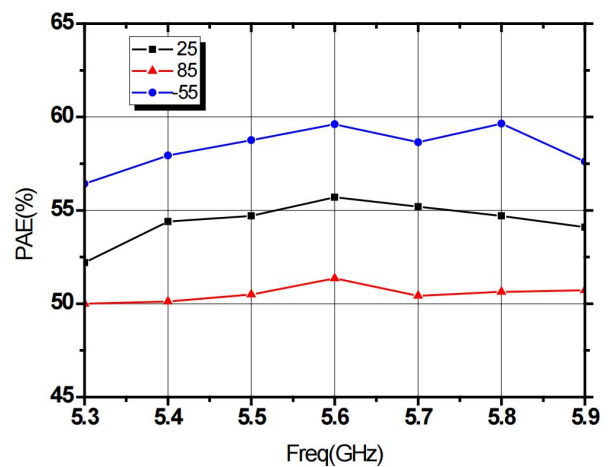
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	57	57.5	-	dBm
Gp	Power Gain	11	11.5	-	dB
η_{add}	Power Added Efficiency	50	52	-	%
ΔGp	Gain Flatness	-0.5	-	+0.5	dB

Test Curves

Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.

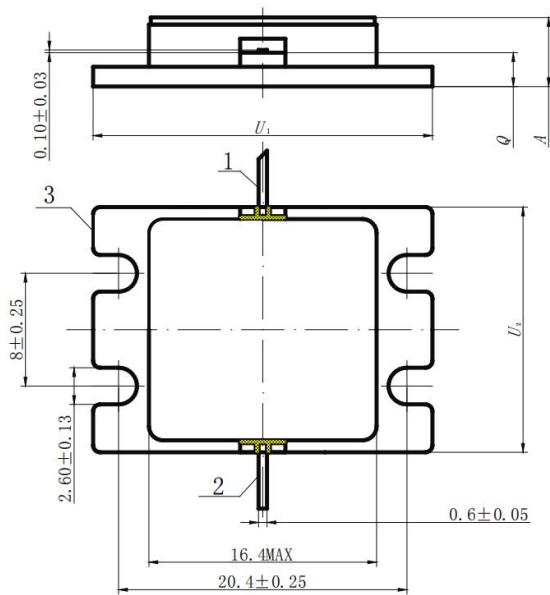


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	60V	
Vg	Grid Voltage	-5V	
Pd	DC Dissipation	1200W	Peak Value
Tch	Channel Temperature	225°C	[1]
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~175°C	

[1] Exceeding any one or combination of these limits may cause permanent damage.

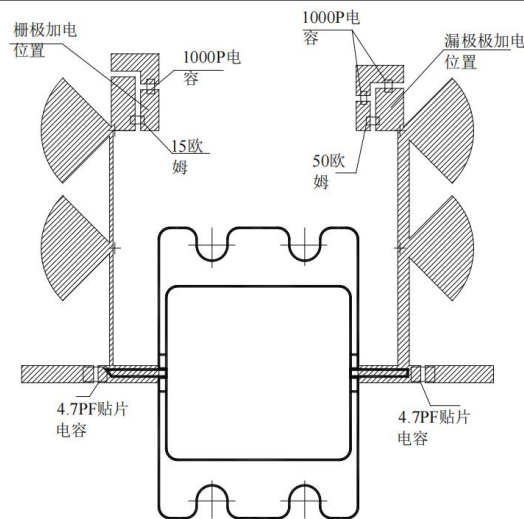
Outline Drawing



Dimension Symbols

Symbol	Value (unit: mm)		
	Min.	Typ.	Max.
U1	23.75	24.00	24.25
U2	17.10	17.40	17.70
A	-	4.70	5.50
Q	2.10	2.40	2.70

Application Circuit



Note:

- (1) This product is an internal matching tube, with input and output impedance values of 50 ohms;
- (2) The power-on sequence shall be in strict accordance with the sequence of applying negative power first and then positive power. When power-off, the leakage voltage shall be reduced first and then the grid voltage shall be reduced;
- (3) This product is a high-power device. Pay attention to heat dissipation during use. The higher the shell temperature is, the shorter the service life is. The service temperature should not be higher than 80 °C;
- (4) This product is an electrostatic sensitive device. It needs to pay attention to electrostatic protection during storage and use, and it needs to be grounded well during use.